

SWITCHING REGULATOR APPLICATIONS

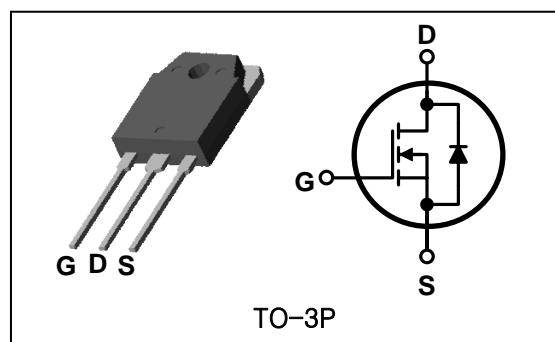
Features

- High Voltage : $BV_{DSS}=500V$ (Min.)
- Low C_{rss} : $C_{rss}=27pF$ (Typ.)
- Low gate charge : $Q_g=65nC$ (Typ.)
- Low $R_{DS(on)}$: $R_{DS(on)}=0.26\Omega$ (Max.)

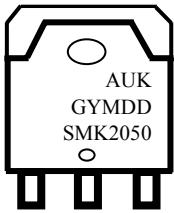
Ordering Information

Type No.	Marking	Package Code
SMK2050CI	SMK2050	TO-3P

PIN Connection



Marking Diagram

	Column 1 : Manufacturer Column 2 : Production Information e.g.) GYMDD - G : Factory management code - YMDD : Date Code (year, month, date) Column 3 : Device Code
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Absolute maximum ratings ($T_c=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	500	V
Gate-source voltage	V_{GSS}	± 30	V
Drain current (DC) *	I_D	($T_c=25^\circ C$) 20 ($T_c=100^\circ C$) 12.6	A
Drain current (Pulsed) *	I_{DM}	80	A
Drain power dissipation	P_D	150	W
Avalanche current (Single) ②	I_{AS}	20	A
Single pulsed avalanche energy ②	E_{AS}	1000	mJ
Avalanche current (Repetitive) ①	I_{AR}	20	A
Repetitive avalanche energy ①	E_{AR}	28	mJ
Junction temperature	T_J	150	$^\circ C$
Storage temperature range	T_{stg}	-55~150	

* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit
Thermal resistance	$R_{th(J-C)}$	-	0.83	$^\circ C/W$
	$R_{th(J-A)}$	-	40	

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0$	500	-	-	V
Gate threshold voltage	$V_{GS(\text{th})}$	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$	3.0	-	5.0	V
Drain-source cut-off current	I_{DSS}	$V_{DS}=500\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
		$V_{DS}=400\text{V}, V_{GS}=0\text{V}$ $T_C=125^\circ\text{C}$	-	-	100	
Gate leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm30\text{V}$	-	-	±100	nA
Drain-source on-resistance ^(④)	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=10\text{A}$	-	0.21	0.26	Ω
Forward transfer conductance ^(④)	g_{fs}	$V_{DS}=10\text{V}, I_D=10\text{A}$	-	24.6	-	S
Input capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=25\text{V},$ $f=1\text{MHz}$	-	3120	-	pF
Output capacitance	C_{oss}		-	355	-	
Reverse transfer capacitance	C_{rss}		-	27	-	
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD}=250\text{V}, I_D=20\text{A}$ $R_G=25\Omega$	-	95	-	ns
Rise time	t_r		-	375	-	
Turn-off delay time	$t_{d(\text{off})}$		-	100	-	
Fall time	t_f		-	105	-	
Total gate charge	Q_g	$V_{DS}=400\text{V}, V_{GS}=10\text{V}$ $I_D=20\text{A}$	-	65	85	nC
Gate-source charge	Q_{gs}		-	17.6	-	
Gate-drain charge	Q_{gd}		③④	-	18.4	-

Source-Drain Diode Ratings and Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	20	A
Source current (Pulsed) ^(①)	I_{SP}		-	-	80	
Forward voltage ^(④)	V_{SD}	$V_{GS}=0\text{V}, I_S=20\text{A}$	-	-	1.4	V
Reverse recovery time	t_{rr}	$I_S=20\text{A}, V_{GS}=0\text{V}$ $dI_S/dt=100\text{A}/\mu\text{s}$	-	507	-	ns
Reverse recovery charge	Q_{rr}		-	7.2	-	μC

Note :

- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② $L=4.5\text{mH}, I_{AS}=20\text{A}, V_{DD}=50\text{V}, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
- ③ Pulse Test : Pulse width $\leq 300\text{us}$, Duty cycle $\leq 2\%$
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

Fig. 1 I_D - V_{DS}

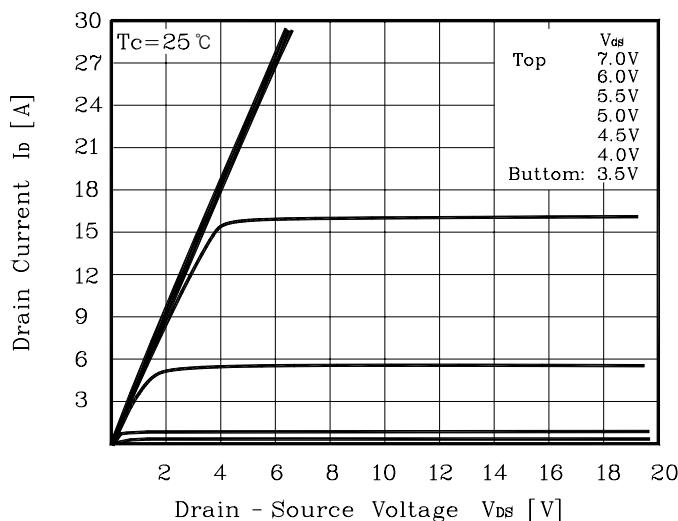


Fig. 2 I_D - V_{GS}

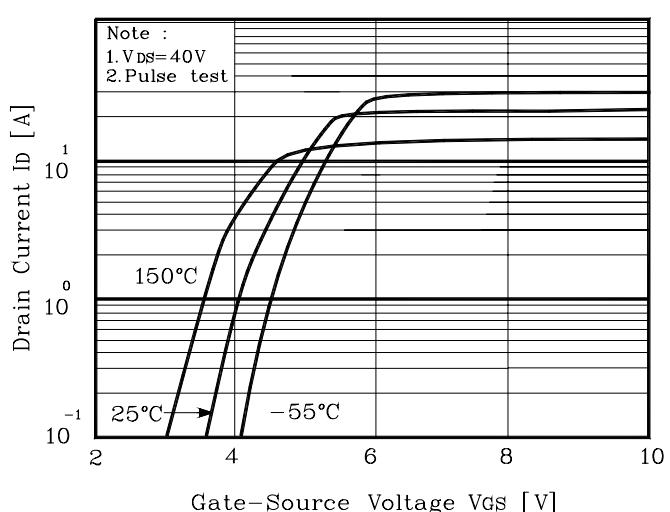


Fig. 3 $R_{DS(on)}$ - I_D

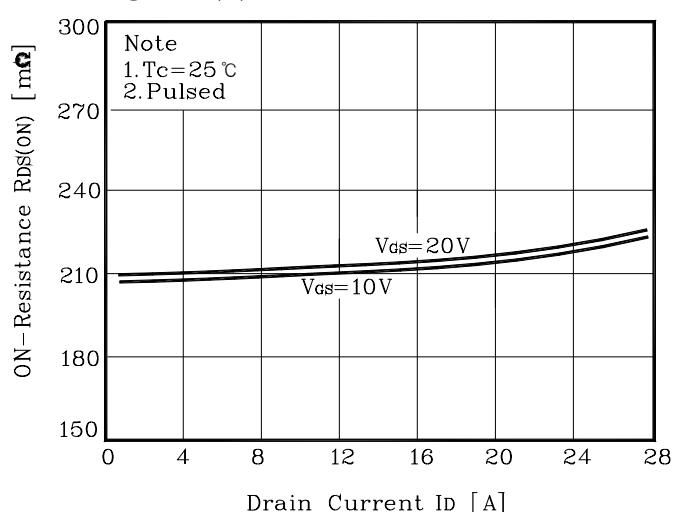


Fig. 4 I_S - V_{SD}

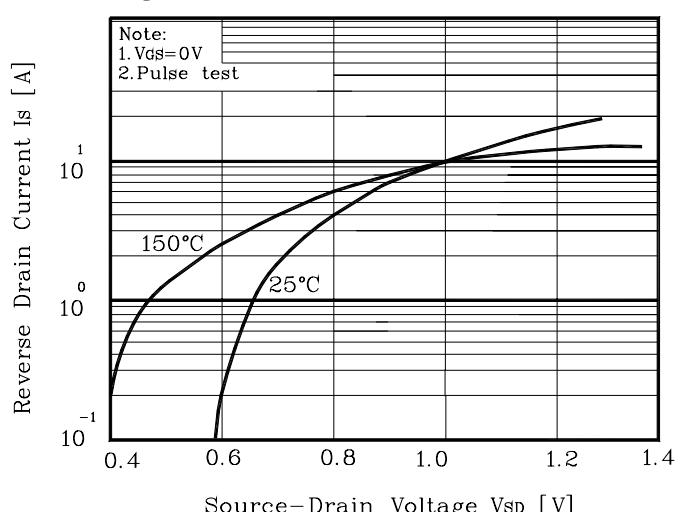


Fig. 5 Capacitance - V_{DS}

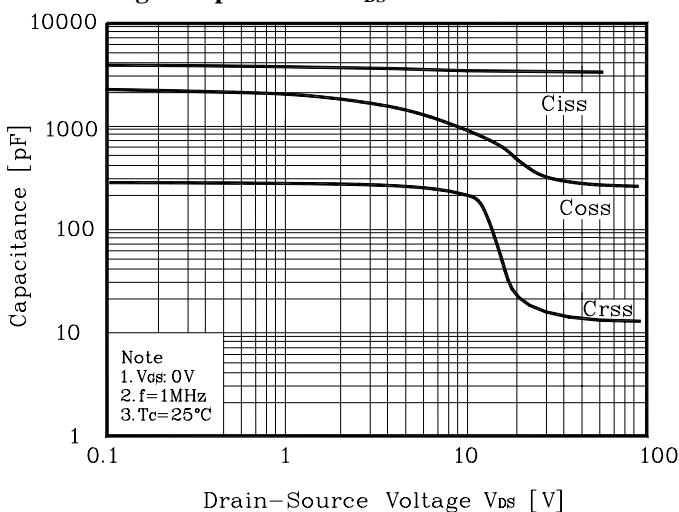
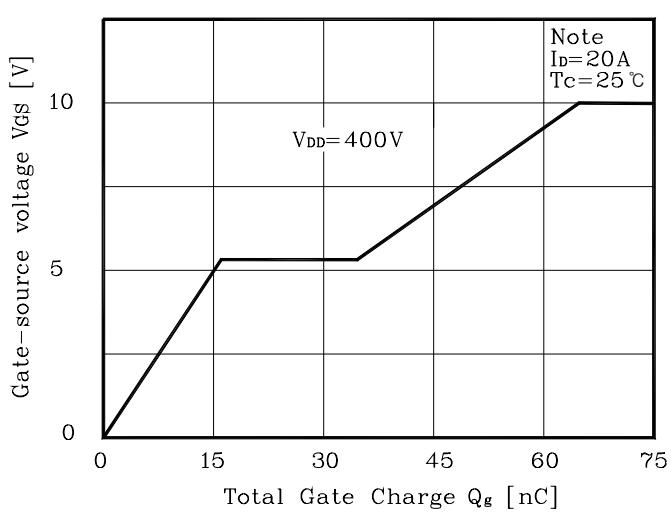


Fig. 6 V_{GS} - Q_G



Electrical Characteristic Curves

Fig. 7 V_{DSS} - T_J

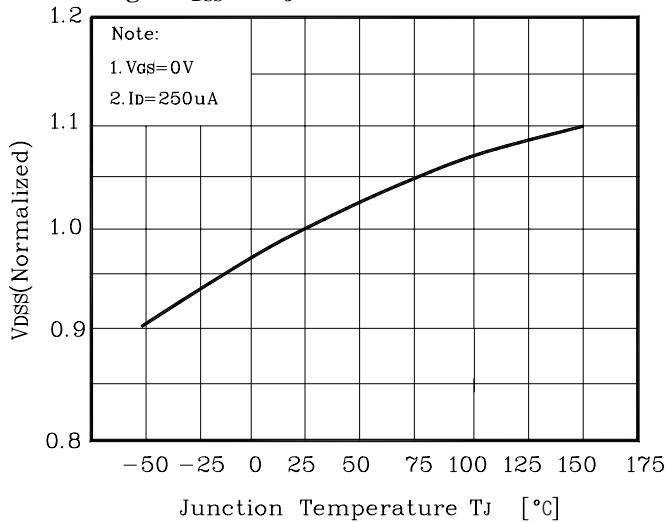


Fig.8 R_{DS(on)} - T_J

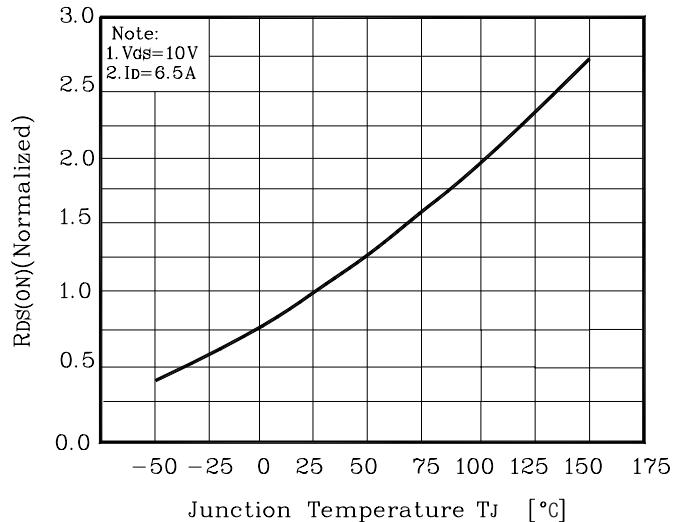


Fig. 9 I_D - T_C

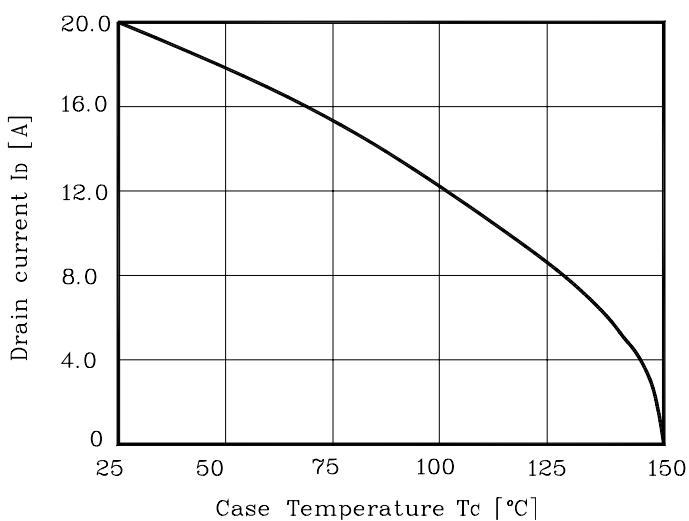


Fig. 10 Safe Operating Area

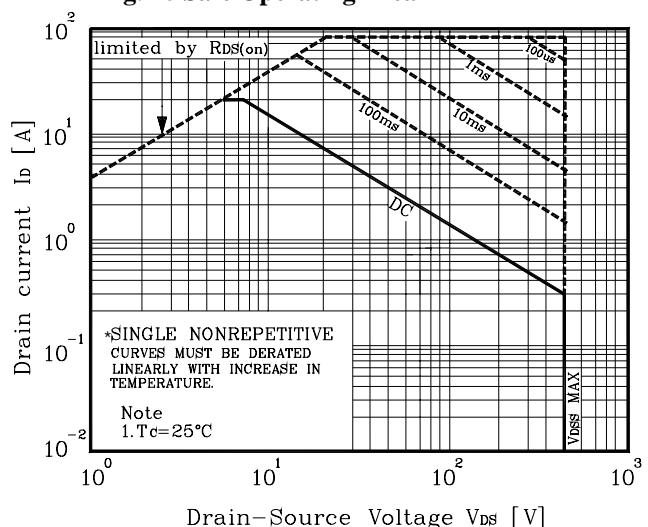


Fig. 11 Gate Charge Test Circuit & Waveform

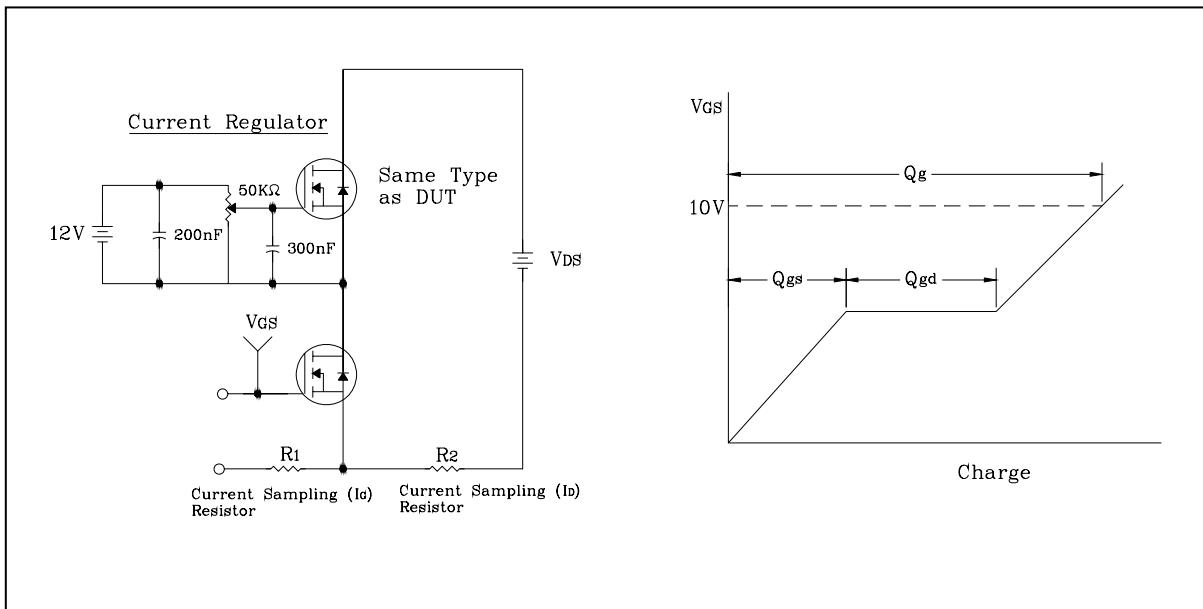


Fig. 12 Resistive Switching Test Circuit & Waveform

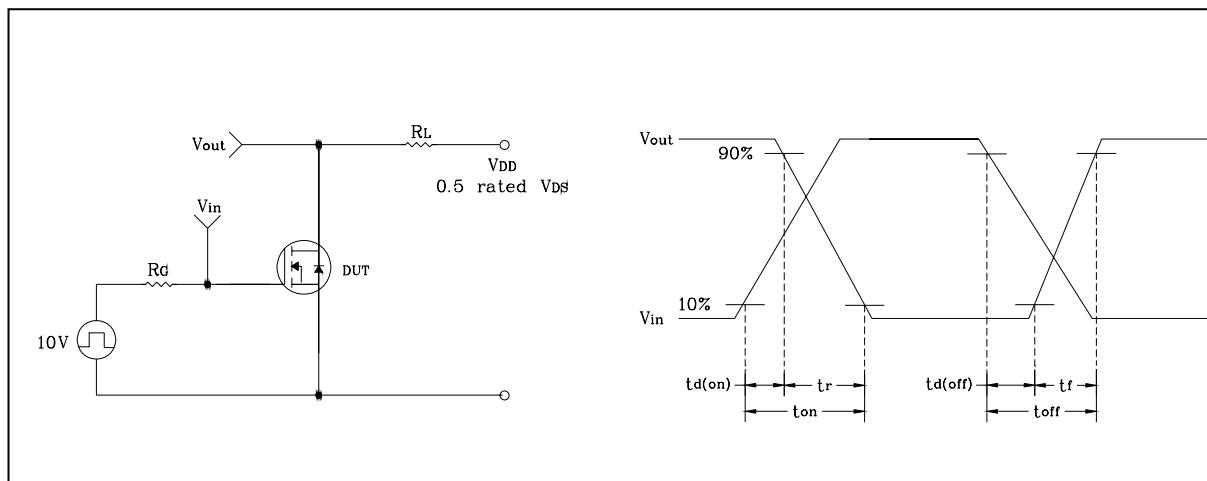


Fig. 13 E_{AS} Test Circuit & Waveform

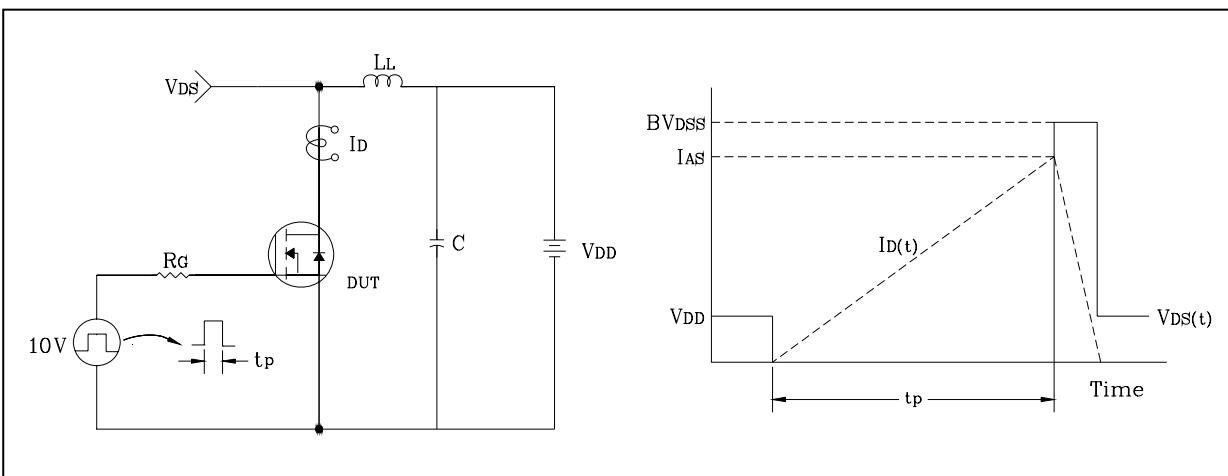
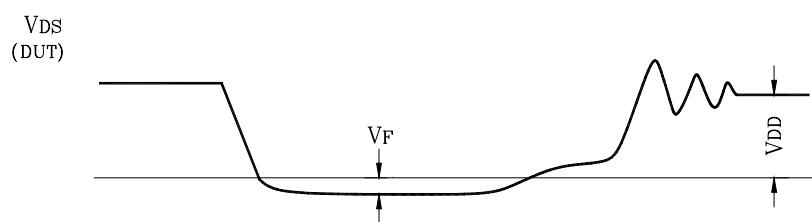
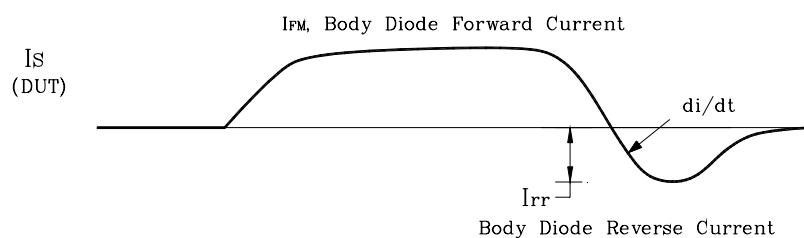
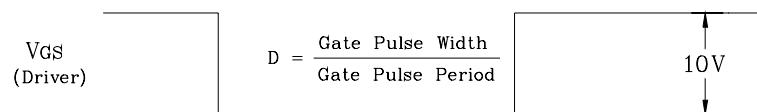
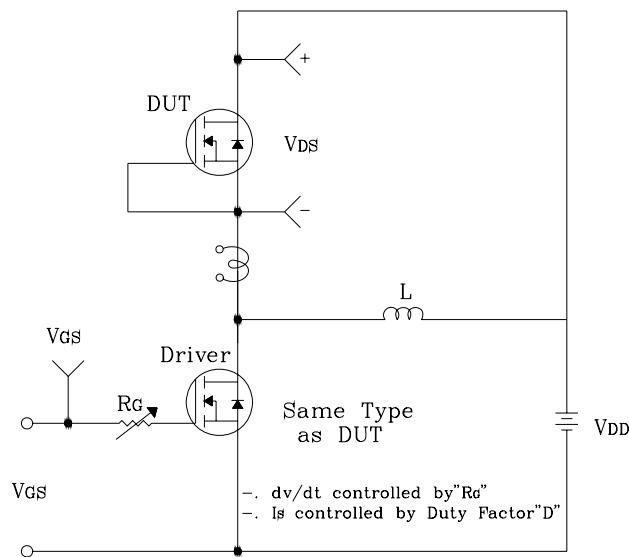
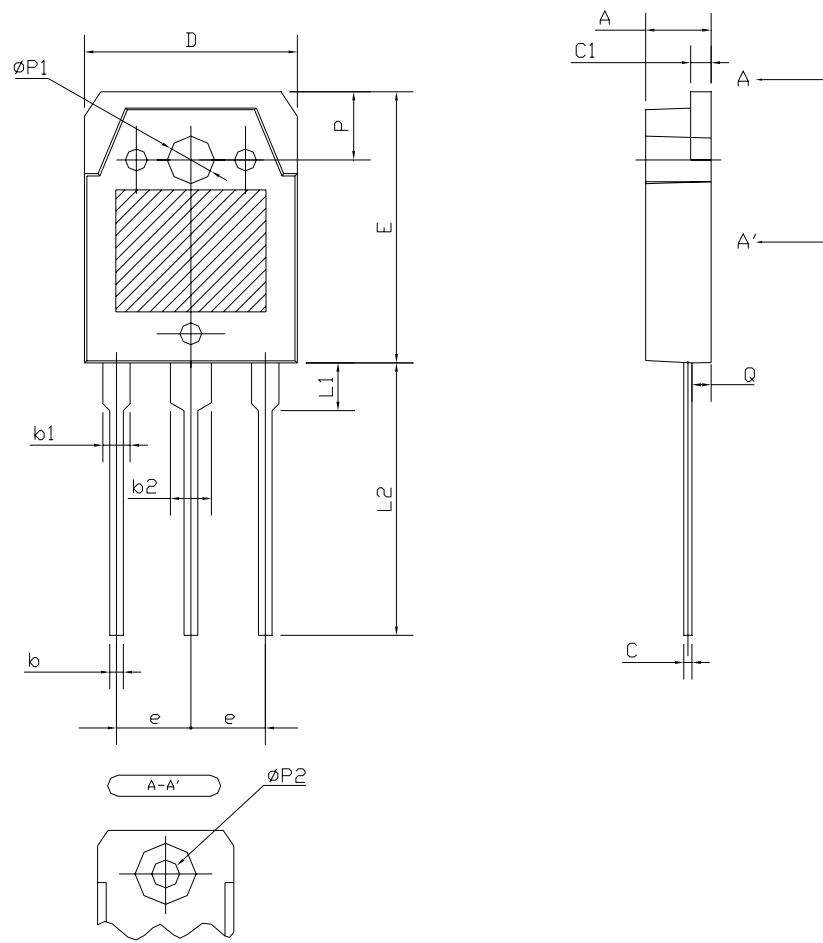


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



Outline Dimension

unit: mm



SYMBOL	MIN	NOM	MAX
A	4.60	4.80	5.00
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
C	0.55	0.60	0.75
C1	1.45	1.50	1.65
D	15.40	15.60	15.80
E	19.70	19.90	20.10
e	5.15	5.45	5.75
L1	3.30	3.50	3.70
L2	19.80	20.00	20.20
P	4.80	5.00	5.20
ϕP_1	3.30	3.40	3.50
ϕP_2	(3.20)		
Q	1.20	1.40	1.60

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